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November 2013

## FQPF7P20

## P-Channel QFET® MOSFET

-200 V, -5.2 A, 690 mΩ

## **Description**

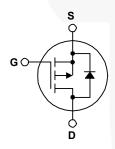
This P-Channel enhancement mode power MOSFET is • -5.2 A, -200 V,  $R_{DS(on)}$  = 690 m $\Omega$  (Max.) @  $V_{GS}$  = -10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state

Low Gate Charge (Typ. 19 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 25 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, • 100% Avalanche Tested DC motor control, and variable switching power applications.

### **Features**

- $I_D = -2.6 A$





## Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	FQPF7P20	Unit
V <sub>DSS</sub>	Drain-Source Voltage	-200	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)	-5.2	Α
	- Continuous (T <sub>C</sub> = 100°C)	-3.3	Α
I <sub>DM</sub>	Drain Current - Pulsed (Note 1)	-20.8	Α
V <sub>GSS</sub>	Gate-Source Voltage	± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)	570	mJ
I <sub>AR</sub>	Avalanche Current (Note 1)	-5.2	А
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	4.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	-5.5	V/ns
$P_{D}$	Power Dissipation (T <sub>C</sub> = 25°C)	45	W
	- Derate above 25°C	0.36	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds.	300	°C

## **Thermal Characteristics**

Symbol	Parameter	FQPF7P20	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.78	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

## **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQPF7P20	FQPF7P20	TO-220F	Tube	N/A	N/A	50 units

## **Electrical Characteristics**

T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V, } I_{D} = -250 \mu\text{A}$	-200			V
ΔBV <sub>DSS</sub> / ΔT	Breakdown Voltage Temperature Coefficient	$I_D$ = -250 μA, Referenced to 25°	C	-0.1		V/°C
I <sub>DSS</sub>	Zon Outs Vallana Busin Outsul	V <sub>DS</sub> = -200 V, V <sub>GS</sub> = 0 V			-1	μΑ
Zero Gate Voltage Drain Current	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -160 V, T <sub>C</sub> = 125°C			-10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
On Cha	aracteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-3.0		-5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -2.6 A		0.54	0.69	Ω
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = -40 \text{ V}, I_{D} = -2.6 \text{ A}$		3.5		S
Dynam	ic Characteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0  MHz		590	770	pF
C <sub>oss</sub>	Output Capacitance			140	180	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			25	35	pF
Switchi	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = -100 V, I <sub>D</sub> = -7.3 A,		15	40	ns
t <sub>r</sub>	Turn-On Rise Time	$R_{G} = 25 \Omega$		110	230	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			30	70	ns
t <sub>f</sub>	Turn-Off Fall Time	(Noat	e 4)	42	90	ns
$Q_g$	Total Gate Charge	$V_{DS} = -160 \text{ V}, I_{D} = -7.3 \text{ A},$		19	25	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = -10 V		4.6		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Noate 4)		9.5		nC
Drain-9	Source Diode Characteristics a	nd Maximum Ratings				
l <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				-5.2	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				-20.8	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -5.2 A			-5.0	V
	Reverse Recovery Time	$V_{GS} = 0 \text{ V, } I_{S} = -7.3 \text{ A,}$		180		ns
t <sub>rr</sub>	TREVEISE RECOVERY TIME	dl <sub>F</sub> / dt = 100 A/μs				

- 1. Repetitive rating : pulse-width limited by maximum junction temperature.
- 2. L = 31.5 mH, I<sub>AS</sub> = -5.2 A, V<sub>DD</sub> = -50 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C. 3. I<sub>SD</sub>  $\leq$  -7.3 A, di/dt  $\leq$  300 A/µs , V<sub>DD</sub>  $\leq$  BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C. 4. Essentially independent of operating temperature.

## **Typical Characteristics**

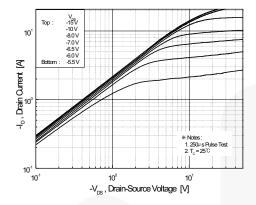


Figure 1. On-Region Characteristics

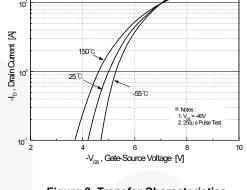


Figure 2. Transfer Characteristics

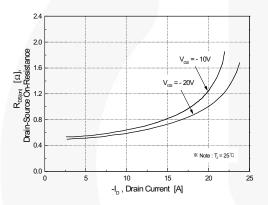


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

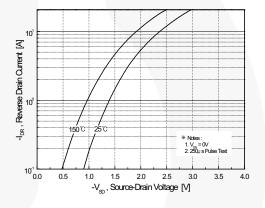


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

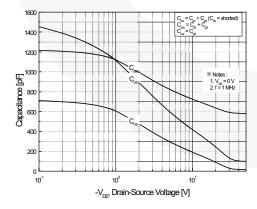


Figure 5. Capacitance Characteristics

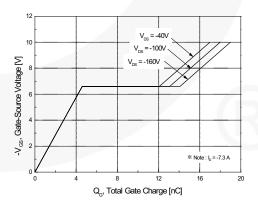


Figure 6. Gate Charge Characteristics

# Typical Characteristics (Continued)

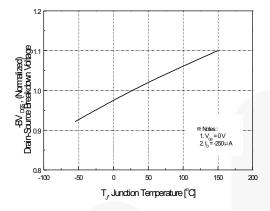


Figure 7. Breakdown Voltage Variation vs. Temperature

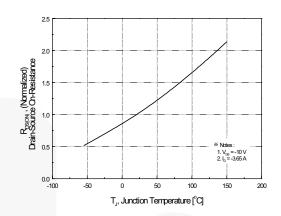


Figure 8. On-Resistance Variation vs. Temperature

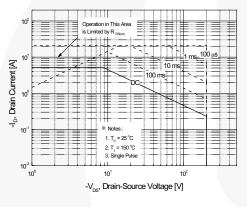


Figure 9. Maximum Safe Operating Area

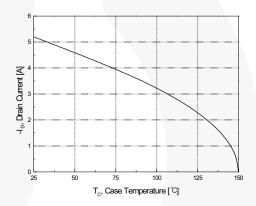


Figure 10. Maximum Drain Current vs. Case Temperature

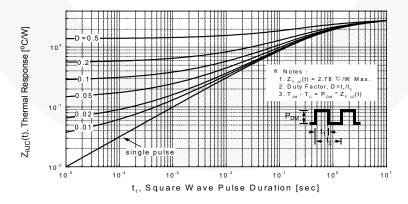


Figure 11. Transient Thermal Response Curve

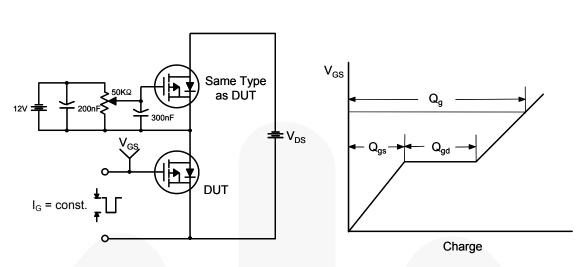


Figure 12. Gate Charge Test Circuit & Waveform

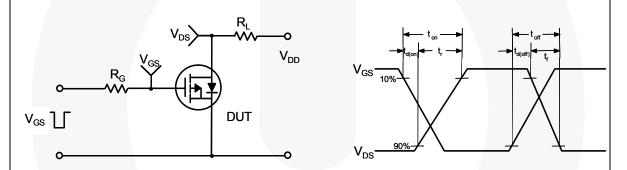


Figure 13. Resistive Switching Test Circuit & Waveforms

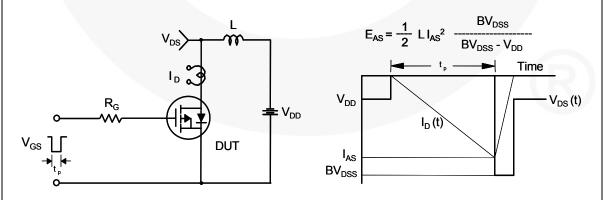
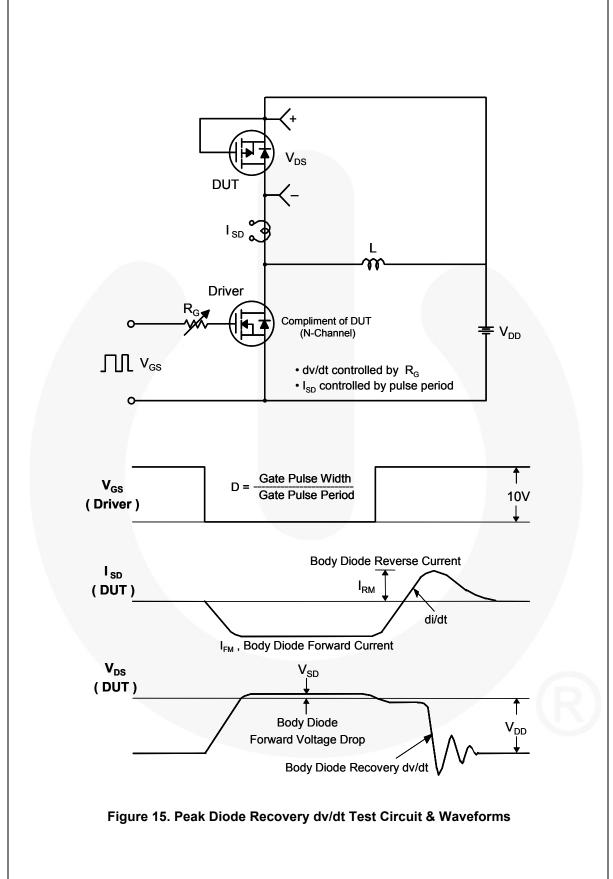


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



## **Mechanical Dimensions**

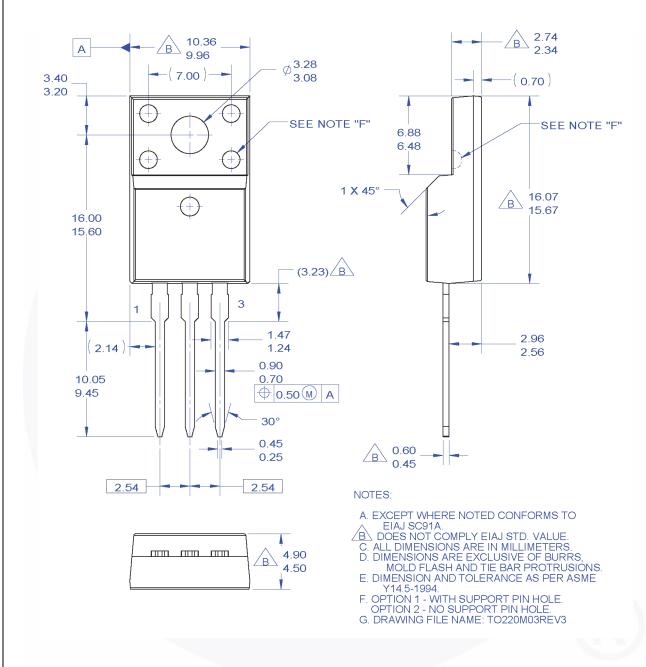


Figure 16. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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